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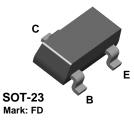
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**BCV26** 



## BCV26



# **PNP** Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
Ic	Collector Current - Continuous	1.2	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		*BCV26	
PD	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

\*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

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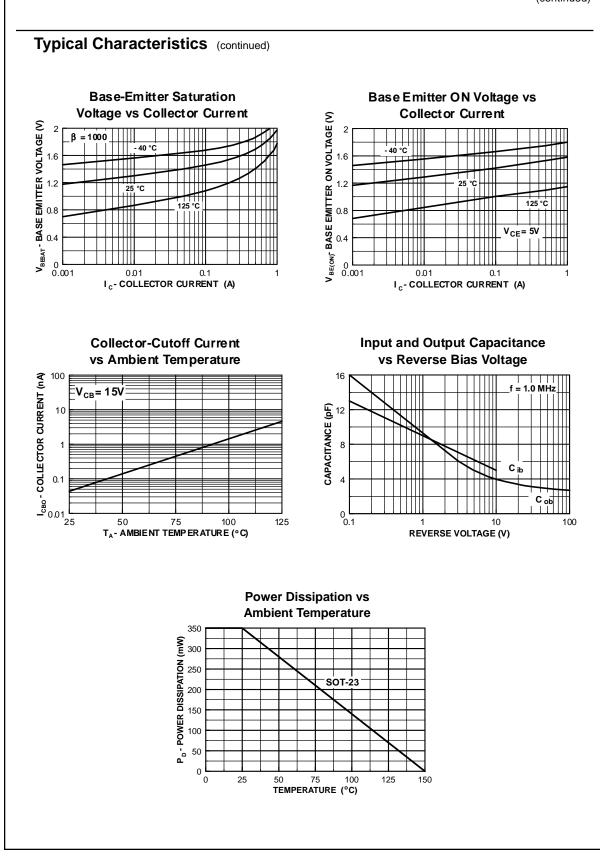
## PNP Darlington Transistor (continued)

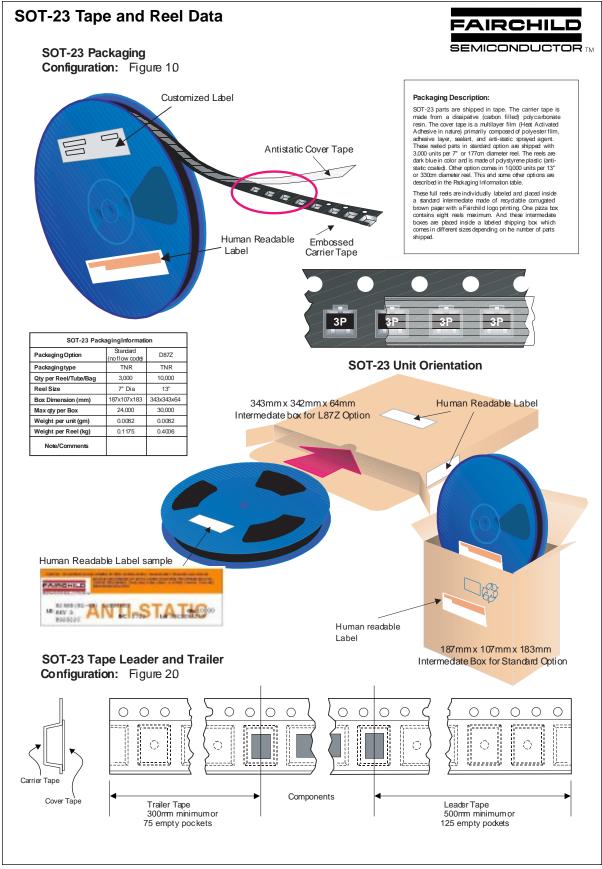
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
	RACTERISTICS					
	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu{\rm A},  I_{\rm E} = 0$	40			v
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \text{ nA}, I_{\rm E} = 0$	10			v
CBO	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0$			0.1	μA
ЕВО	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$			0.1	μΑ
EBO					011	μ
ON CHAR	ACTERISTICS					
E	DC Current Gain $I_c = 1.0 \text{ mA}, V_{ce} = 5.0 \text{ V}$		4,000			
		$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$	10,000			
	Collector-Emitter Saturation Voltage	$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, I_{B} = 0.1 \text{ mA}$	20,000		1.0	V
CE(sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$			1.5	V
BE(sat)	Dase-Emilier Galdrailon Voltage	$I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA			1.5	v
С С	Current Gain - Bandwidth Product Collector Capacitance ages (V) and currents (A) are negative polarity for PNP	$\label{eq:loss} \begin{array}{l} I_{C} = 30 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f = 100 \text{ MHz} \\ \\ V_{CB} = 30 \text{ V}, \ I_{E} = 0, \ f = 1.0 \text{ MHz} \end{array}$ transistors.		220 3.5		pF
NOTE: All volta	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP	f = 100 MHz V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0, f = 1.0 MHz				
	Collector Capacitance	f = 100 MHz V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0, f = 1.0 MHz				
Note: All volta	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP	$\begin{array}{c c} f = 100 \text{ MHz} \\ \hline V_{CB} = 30 \text{ V}, \text{ I}_{\text{E}} = 0, \text{ f} = 1.0 \text{ MHz} \\ \end{array}$ transistors.	Emitter	3.5	ation	
Note: All volta	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP al Characteristics	$\begin{array}{c c} f = 100 \text{ MHz} \\ \hline V_{CB} = 30 \text{ V}, \text{ I}_{\text{E}} = 0, \text{ f} = 1.0 \text{ MHz} \\ \end{array}$ transistors.		3.5 Satur		
Note: All volta	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current	$\begin{array}{c c} f = 100 \text{ MHz} \\ \hline V_{CB} = 30 \text{ V}, \text{ I}_{\text{E}} = 0, \text{ f} = 1.0 \text{ MHz} \\ \end{array}$ transistors.		3.5 Satur		
Note: All volta	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain	$\begin{array}{c c} f = 100 \text{ MHz} \\ \hline V_{CB} = 30 \text{ V}, \text{ I}_{\text{E}} = 0, \text{ f} = 1.0 \text{ MHz} \\ \end{array}$ transistors.		3.5 Satur		
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CC NOTE: All volta Typica 50 50 40 40	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current	$f = 100 \text{ MHz}$ $V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ transistors. Collector- Voltage vs $I.6$ $B = 1000$ $B = 1000$ $B = 1000$ $B = 1000$		3.5 Satur		
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CC NOTE: All volta Typica 50 50 40 40	Collector Capacitance         ages (V) and currents (A) are negative polarity for PNP         al Characteristics         Typical Pulsed Current Gain vs Collector Current         v <sub>CE</sub> = 5v         125 °C         25 °C	$f = 100 \text{ MHz}$ $V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ transistors. Collector- Voltage vs $I.6$ $B = 1000$ $B = 1000$ $B = 1000$ $B = 1000$		3.5 Satur etor Cu	rrent	
CC NOTE: All volta Typica 50 50 40 40	Collector Capacitance         ages (V) and currents (A) are negative polarity for PNP         al Characteristics         Typical Pulsed Current Gain vs Collector Current         V <sub>CE</sub> = 5V	$f = 100 \text{ MHz}$ $V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ transistors. Collector- Voltage vs $I.6$ $B = 1000$ $B = 1000$ $B = 1000$ $B = 1000$		3.5 Satur etor Cu	rrent	
Note: All volta	Collector Capacitance         ages (V) and currents (A) are negative polarity for PNP         al Characteristics         Typical Pulsed Current Gain vs Collector Current         v <sub>CE</sub> = 5v         125 °C         25 °C	$f = 100 \text{ MHz}$ $V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ transistors. Collector- Voltage vs $I.6$ $f = 100$ $f = 100$ $f = 100$		3.5 Satur etor Cu	rrent	

PNP Darlington Transistor (continued)

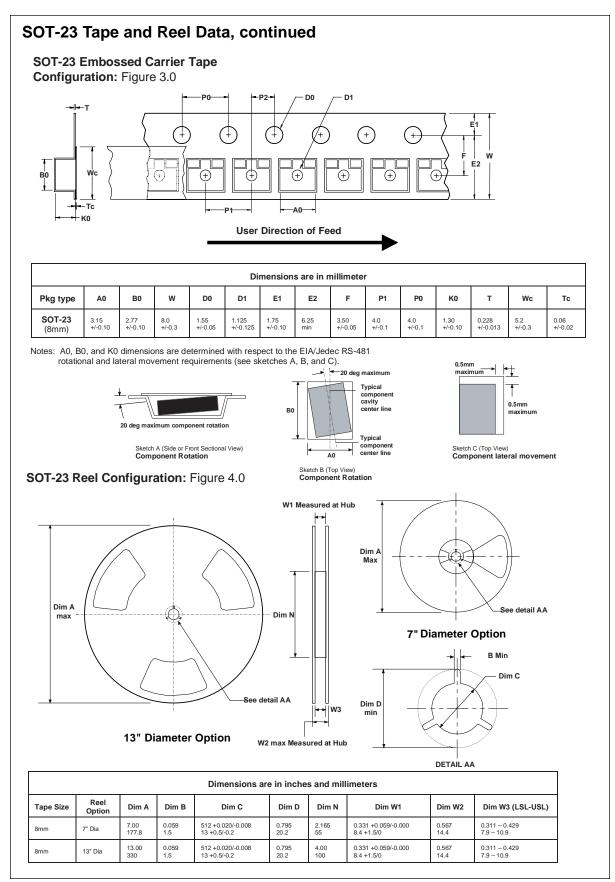
# BCV26



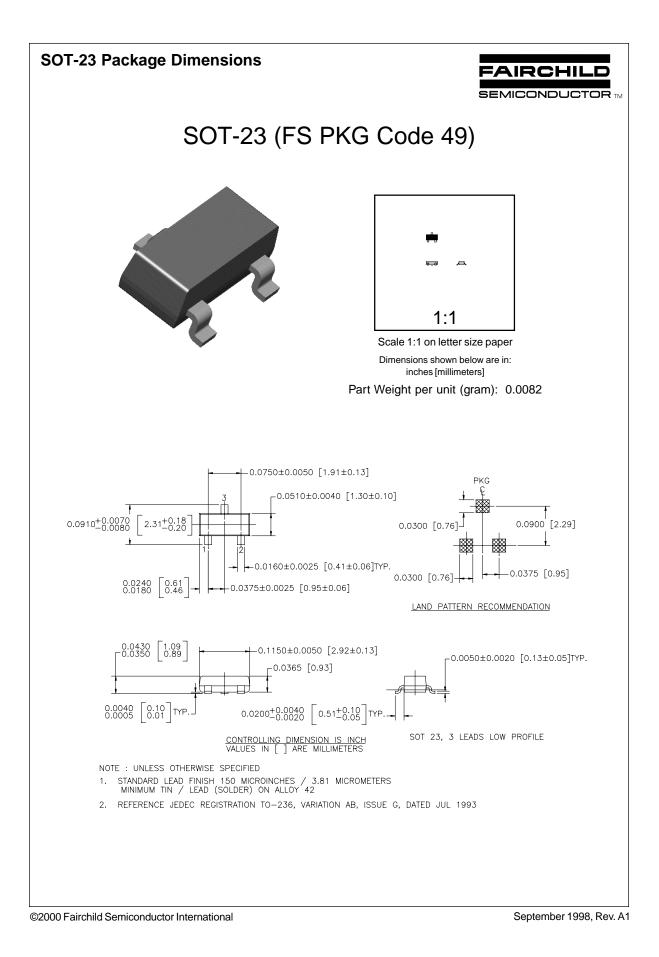


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